FG N	PTO	-14	49

INFORMATION DISCLOSURE CITATION Express Mail Number Express Mail

(Use several sheets if necessary)

Docket Number (Optional)
072219-0278259
(P05108)

Application No. New

Applicant(s)

Filing Date

Herewith

Heikyung Min et al.

Group Art Unit Unknown



							U.	S. PATEN	IT DOCUMEN	TS				
EXAMINER INITIAL	DO	CUI	ΜEN [*]	T NU	МВ	ER	DATE NAME				CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
						T							AFFROF	MAIL
							-					-		
							-							
						\dashv								
									· · ·			1		
					-									
			_											
										,				
							FOR	EIGN PAT	ENT DOCUME	NTS				
	DOCUMENT NUMBER					IBER	DAT	DATE COUNTRY		CLASS	SUBCLASS	Translation Yes No		
						T							res	INO
						-								
					_									 -
									· · · · · · · · · · · · · · · · · · ·					
			i			<u> </u>								
				THE	R D	ocui	MENTS (Inc	luding A	uthor, Title, Da	ate, Pe	rtinent Pages	, Etc.)		
	James Dunkley et al., "Hot Electron Induced Hydrogen Compensation of Boron Doped Silicon Resulting From Emitter-Base Breakdown", IEEE, 1992, pps. 31.4.1 – 31.4.3.													
Bu	M.	Solt	ani-l	Farsh	i et	al.,"	Thermal Be	naviour of	Implanted Ni	trogen		ated Hydrogen		m",
												237. ftening in Alph		,"
L.	O.N. Senkov and J.J. Jonas, "Dynamic Strain Aging and Hydrogen-Induced Softening in Alpha Titanium", Metallurgical and Materials Transactions A, Volume 27A, July 1996, pps. 1877-1887.													
EXAMINER) mig ful (DATE CONSIDERED 7/02														
EXAMINER: In	nitial	if ci	tatio	h co	nsic	lered,	whether o	r not cita	tion is in conf	ormanc	e with MPEP	§609; Draw lin	ne through	,
citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.														

PTO/SB/08 (10-92)

Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE